Easteh HET 03/06/05. # (11pp.)

				10010		7	
Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp	
L2	60	separate near1 gate and TFT	US-PGPUB	OR	OFF	2005/03/06 1	2:25
L3	654	double adj gate and tft	US-PGPUB	OR	OFF	2005/03/06 1	2:26
L4	15	double adj gate.ti,ab,clm. and tft	US-PGPUB	OR	OFF	2005/03/06 1	2:48
L5	2	(overlap overlapping) near6 gate near6 (".mu.m" ".ANG." nm nanometer micron) and tft.ti,ab, clm.	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 1	3:01
L6	7	(overlap overlapping) near6 gate near6 (".mu.m" ".ANG." nm nanometer micron) and tft	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 1	3:36
L7	83	(overlap overlapping) near6 (".mu. m" ".ANG." nm nanometer micron) and tft	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 1	3:36
L15	10	(JP-2003045892-\$ or JP-2000353811-\$ or JP-05335573-\$ or JP-11307777-\$ or JP-08250742-\$).did. or (JP-2000353811-\$ or US-20030025127-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-05335573-\$).did.	JPO; DERWENT	OR	OFF	2005/03/06 1	3:50
L16	11	(JP-2003045892-\$ or JP-2000353811-\$ or JP-05335573-\$ or JP-11307777-\$ or JP-08250742-\$).did. or (JP-2000353811-\$ or US-20030025127-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-05335573-\$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/06 1	3:52
L17	266	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/06 1	3:52
L18	144	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 1	3:52
L19	47	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 1	3:56

L20	7	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain near6 ("mu.m" nm ".ANG.") and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:57
S1	2	jp-05335573\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:36
S2	0	jp-200345892\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S3	2	jp-2003045892\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S4	2	jp-08250742\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S5	2	jp-11307777\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S6	2	jp-2000353811\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:41
\$7	10	S1 S2 S3 S4 S5 S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:41
S8	5	"773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:44
S9	18	(tft thin adj film adj transistor) and overlap near6 ("low" "high") near2 voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:05

S10	4455	"low" near2 voltage and "high" near2 voltage and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:09
S11	80	"low" near2 voltage near20 gate adj (insulation insulating oxide) and "high" near2 voltage near20 gate adj (insulation insulating oxide) and (tft:thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:10
S12	5683	((257/59) or (257/72) or (257/351) or (257/355) or (257/356) or (257/390) or (257/391) or (257/393) or (257/393) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT	OR	OFF .	2005/03/05 17:39
S13	19	S12 and gate adj insulat\$3.clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:44
S14	133	(257/406).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 17:44

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S15	42	(US-20040195568-\$ or	US-PGPUB;	OR	OFF	2005/03/05 18:05
		US-20040046174-\$ or	USPAT;			
		US-20030025127-\$ or	JPO;			
		US-20020149056-\$ or	DERWENT	1		
		US-20020135554-\$ or				
		US-20020042170-\$ or				
		US-20020041350-\$ or				
`		US-20020030190-\$ or				
		US-20020024048-\$ or				
		US-20010013912-\$ or				
		US-20010000755-\$ or		-		
		US-20040026750-\$ or				
		US-20020084490-\$).did. or				
		(US-6856360-\$ or US-6657228-\$				
		or US-6452211-\$ or US-6426787-\$				
		or US-6420988-\$ or US-6400434-\$				
		or US-6384886-\$ or US-6368904-\$				
		or US-6316787-\$ or US-6303963-\$				
		or US-6294815-\$ or US-6165824-\$				
ļ		or US-6163055-\$ or US-6115094-\$				
		or US-5528056-\$ or US-6597046-\$				
		or US-5468987-\$).did. or				
		(JP-2003045892-\$ or				
		JP-2000353811-\$ or				
1		JP-11307777-\$ or JP-08250742-\$				
		or JP-05335573-\$ or				
		JP-54015678-\$ or				
		JP-02222169-\$).did. or				
		(US-20030025127-\$ or				
		JP-2000353811-\$ or				
		JP-11307777-\$ or JP-08250742-\$				
		or JP-05335573-\$).did.	***************************************			
S16	317	(257/391).CCLS.	US-PGPUB;	OR	OFF	2005/03/05 18:06
			USPAT			

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S17	46	(US-20040195568-\$ or US-20040046174-\$ or US-20030025127-\$ or US-20020149056-\$ or US-20020042170-\$ or US-20020042170-\$ or US-20020041350-\$ or US-20020024048-\$ or US-20020024048-\$ or US-20010013912-\$ or US-20010013912-\$ or US-20020084490-\$ or US-20020117723-\$).did. or (US-6856360-\$ or US-6657228-\$ or US-6420988-\$ or US-6426787-\$ or US-6420988-\$ or US-6303963-\$ or US-6316787-\$ or US-6303963-\$ or US-6294815-\$ or US-6165824-\$ or US-636897-\$ or US-6576556-\$).did. or (US-5576556-\$).did. or (US-5576556-\$).did. or (US-2003045892-\$ or US-6541823-\$ or US-5468987-\$ or US-6541823-\$ or US-5576578-\$ or US-6541823-\$ or US-557656-\$).did. or (US-2003045892-\$ or US-1307777-\$ or JP-08250742-\$ or JP-02222169-\$).did. or (US-20030025127-\$ or JP-1307777-\$ or JP-08250742-\$ or JP-05335573-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:33
S18	5	S17 and double adj gate	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:35
S19	2	S17 and ((additional extra second double) adj gate sub-gate) near5 (withstand break-down breakdown) near2 voltage	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:47
S20	326	(257/392).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:57
S21	138	(257/270).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:59
S22	264	(257/346).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 19:06
S23	159	(257/387).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 19:06

S24	5	"low" near1 voltage near10 (tft thin adj film adj transistor) near10 (self-alignment selfaligned overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	OFF	2005/03/05 19:14
			IBM_TDB			

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S25	82	(US-20040195568-\$ or	US-PGPUB;	OR	OFF	2005/03/05 19:19
		US-20040046174-\$ or	USPAT;	İ		
		US-20030025127-\$ or	JPO;			
		US-20020149056-\$ or	DERWENT			
		US-20020135554-\$ or				
		US-20020042170-\$ or				}
	ļ	US-20020041350-\$ or				
	İ	US-20020041330-\$ or				
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	i	US-20020024048-\$ or				
	ļ	US-20010013912-\$ or				
		US-20010000755-\$ or				
	ĺ	US-20040026750-\$ or				
		US-20020084490-\$ or				
		US-20020190343-\$ or			1	
		US-20020117723-\$ or				
		US-20030132500-\$).did. or				
		(US-6856360-\$ or US-6657228-\$				
		or US-6452211-\$ or US-6426787-\$			İ	
		or US-6420988-\$ or US-6400434-\$				
		or US-6384886-\$ or US-6368904-\$				
		or US-6316787-\$ or US-6303963-\$				
		or US-6294815-\$ or US-6165824-\$				
		or US-6163055-\$ or US-6115094-\$				
		or US-5528056-\$ or US-6597046-\$				
		or US-5468987-\$ or US-6541823-\$				
		or US-5576556-\$ or US-6847080-\$				
		or US-6847088-\$ or US-6853030-\$				
		or US-6770940-\$ or US-6653694-\$	į			
		or US-6646313-\$ or				
		US-6627963-\$).did. or	***			
	ĺ	(US-6593191-\$ or US-6586805-\$				·
		, , ,	-			
		or US-6579736-\$ or US-6563182-\$				
		or US-6559489-\$ or US-6492690-\$				
		or US-6380590-\$ or US-6333541-\$,	
:		or US-6300663-\$ or US-6271572-\$				
		or US-6267479-\$ or US-6265739-\$				
		or US-6251732-\$ or US-6198140-\$				
		or US-6191460-\$ or US-6175138-\$				
l i		or US-6166417-\$ or US-6093594-\$,
		or US-5696400-\$ or US-5654577-\$			· ,	
	İ	or US-4205330-\$ or US-4183040-\$				
		or US-4104784-\$ or US-4085498-\$,	
		or US-6157062-\$ or US-6064096-\$				
		or US-5736750-\$).did. or				*
		(US-6469348-\$).did. or				
	ŀ	(JP-2003045892-\$ or				
]	JP-2000353811-\$ or				
	İ	JP-11307777-\$ or JP-08250742-\$	1			
	İ	or JP-05335573-\$ or	ŀ			
		JP-54015678-\$ or				
	ļ	JP-02222169-\$).did. or	1			
		(US-20030025127-\$ or	l			
	İ	JP-2000353811-\$ or				
	ļ	JP-11307777-\$ or JP-08250742-\$	1		-	
	ĺ	or JP-05335573-\$).did.	.			
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S26	10	(JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or JP-2003045892-\$).did. or (JP-05335573-\$ or JP-08250742-\$ or JP-11307777-\$ or JP-2000353811-\$ or US-20030025127-\$).did.	JPO; DERWENT	OR	OFF	2005/03/05 19:43
S27	1	("6509602").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:51
S28	14	S25 and (overlap overlapping) near4 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:52
S29	1	ikeda.in. and yamazaki.in. and thinner.ab. and gate and pixel and TFT.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 20:16
S30	465	(overlap overlapping) near10 (self-alignment self-aligned) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR _.	OFF	2005/03/05 21:34
531	207	(overlap overlapping) near4 (self-alignment self-aligned) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:34
S32	102	(overlap overlapping) near4 (self-alignment self-aligned) near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:35
S33	22	(overlap overlapping) near4 (self-alignment self-aligned) near4 gate and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:35

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S34	82	(US-20010000755-\$ or	US-PGPUB;	OR	OFF	2005/03/06 07:33
		ÙS-20010013912-\$ or	USPAT;			
		US-20020024048-\$ or	JPO;	1		
		US-20020030190-\$ or	DERWENT			
		US-20020041350-\$ or	DERWEIT			
		US-20020041330-\$ or				
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		US-20020084490-\$ or		1		
		US-20020117723-\$ or				
		US-20020135554-\$ or		•		
	l	US-20020149056-\$ or			}	
		US-20020190343-\$ or				
		US-20030025127-\$ or				
		US-20030132500-\$ or				
		US-20040026750-\$ or				
		US-20040046174-\$ or				
	l	US-20040195568-\$).did. or			0	
		(US-4085498-\$ or US-4104784-\$				
		or US-4183040-\$ or US-4205330-\$				
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]		or US-5468987-\$ or US-5528056-\$				
		or US-5576556-\$ or US-5654577-\$				
		or US-5696400-\$ or US-5736750-\$				
		or US-6064096-\$ or US-6093594-\$		-		
		or US-6115094-\$ or US-6157062-\$				
-		or US-6163055-\$ or US-6165824-\$				
		or US-6166417-\$ or US-6175138-\$				
		or US-6191460-\$ or US-6198140-\$				
		or US-6251732-\$ or US-6265739-\$				
		or US-6267479-\$ or US-6271572-\$				
		or US-6294815-\$ or				
1		US-6300663-\$).did. or				
		(US-6303963-\$ or US-6316787-\$				
	-	or US-6333541-\$ or US-6368904-\$				
		or US-6380590-\$ or US-6384886-\$				
		or US-6400434-\$ or US-6420988-\$				
		or US-6426787-\$ or US-6452211-\$				`
		or US-6469348-\$ or US-6492690-\$				
	ļ	or US-6541823-\$ or US-6559489-\$				
		or US-6563182-\$ or US-6579736-\$				
		or US-6586805-\$ or US-6593191-\$				
		or US-6597046-\$ or US-6627963-\$				
		or US-6646313-\$ or US-6653694-\$				
		or US-6657228-\$ or US-6770940-\$		i		
		or US-6847080-\$ or US-6847088-\$				
		or US-6853030-\$).did. or				
		(US-6856360-\$).did. or	İ			
	1	(JP-02222169-\$ or JP-05335573-\$				
	ĺ	or JP-08250742-\$ or				
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	l	JP-2000353811-\$ or				
	ļ	JP-2003045892-\$ or				
	İ	JP-54015678-\$).did. or				
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		(JP-05335573-\$ or JP-08250742-\$				~
		or JP-2000353811-\$ or				
		JP-11307777-\$ or		i	ļ	
Ll		US-20030025127-\$).did.				

S35	. 3	S34 and yanai.in.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/06 07:40
S36	28	(self-aligned self-aligning self-alignment) near10 (".ANG." ". mu.m" micron nm nanometer Angstrom) and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:45
S37	22	(self-aligned self-aligning self-alignment) and LDD and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:55
S38	15	(self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:56
S39	15	(self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and "high" near1 voltage and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:05
S40	126	LDD near4 "low" near1 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:05
S41		LDD near4 "low" near1 voltage and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:36
542	5	LDD near4 "low" near1 voltage and tft and (self-aligned self-aligning self-alignment selfaligned selfaligment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:36
S43	238	second adj electrode near6 TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 10:21

S44	19	split-gate and TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 10:27
S45		separate near1 gate and TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 12:22